

isc Silicon NPN Darlington Power Transistor

BDX85/A/B/C

DESCRIPTION

- High DC Current Gain-
: $h_{FE} = 750(\text{Min}) @ I_C = 3A$
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 45V(\text{Min})$ - BDX85; $60V(\text{Min})$ - BDX85A
 $80V(\text{Min})$ - BDX85B; $100V(\text{Min})$ - BDX85C
- Complement to Type BDX86/A/B/C
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

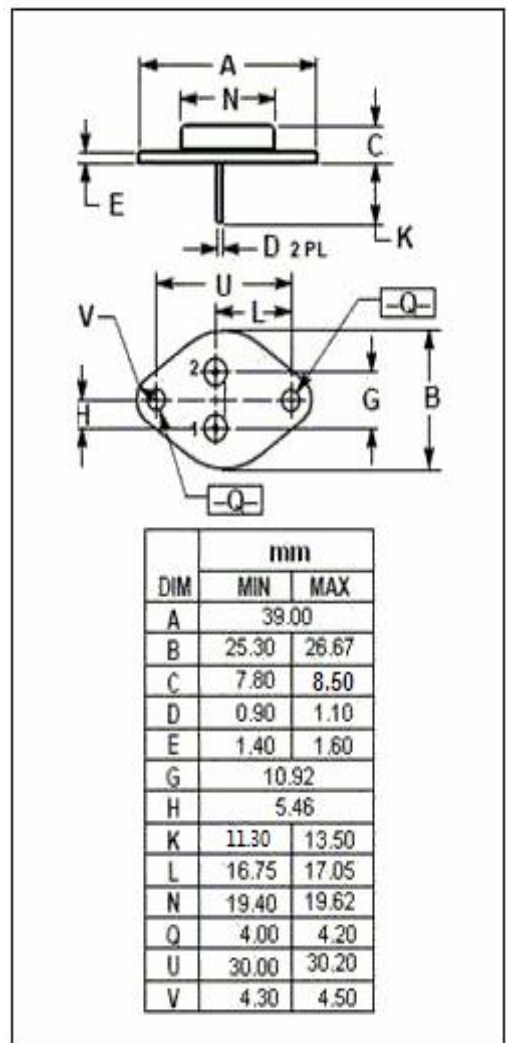
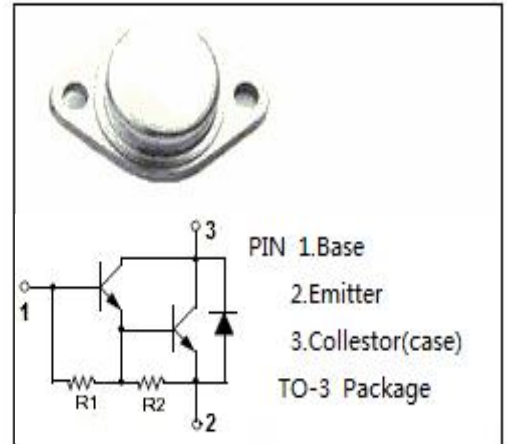
- Designed for use in power linear and switching applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	BDX85	45
		BDX85A	60
		BDX85B	80
		BDX85C	100
V_{CEO}	Collector-Emitter Voltage	BDX85	45
		BDX85A	60
		BDX85B	80
		BDX85C	100
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	10	A
I_{CM}	Collector Current-Peak	15	A
I_B	Base Current	100	mA
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	100	W
T_J	Junction Temperature	200	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65~200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.75	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(SUS)}$	Collector-Emitter Sustaining Voltage	BDX85	45			V
		BDX85A	60			
		BDX85B	80			
		BDX85C	100			
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=4\text{A}; I_B=16\text{mA}$			2.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=8\text{A}; I_B=40\text{mA}$			4.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=8\text{A}; I_B=80\text{mA}$			4.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C=4\text{A}; V_{CE}=3\text{V}$			2.8	V
I_{CBO}	Collector Cutoff Current	BDX85 $V_{CB}=45\text{V}; I_E=0$ $V_{CB}=45\text{V}; I_E=0; T_C=150^{\circ}\text{C}$			0.5 5.0	mA
		BDX85A $V_{CB}=60\text{V}; I_E=0$ $V_{CB}=60\text{V}; I_E=0; T_C=150^{\circ}\text{C}$			0.5 5.0	
		BDX85B $V_{CB}=80\text{V}; I_E=0$ $V_{CB}=80\text{V}; I_E=0; T_C=150^{\circ}\text{C}$			0.5 5.0	
		BDX85C $V_{CB}=100\text{V}; I_E=0$ $V_{CB}=100\text{V}; I_E=0; T_C=150^{\circ}\text{C}$			0.5 5.0	
I_{CEO}	Collector Cutoff Current	BDX85 $V_{CE}=22\text{V}; I_B=0$			1.0	mA
		BDX85A $V_{CE}=30\text{V}; I_B=0$				
		BDX85B $V_{CE}=40\text{V}; I_B=0$				
		BDX85C $V_{CE}=50\text{V}; I_B=0$				
I_{EBO}	Emitter Cutoff Current	$V_{EB}=5\text{V}; I_C=0$			2.0	mA
h_{FE-1}	DC Current Gain	$I_C=3\text{A}; V_{CE}=3\text{V}$	1000			
h_{FE-2}	DC Current Gain	$I_C=4\text{A}; V_{CE}=3\text{V}$	750		18000	
h_{FE-3}	DC Current Gain	$I_C=8\text{A}; V_{CE}=4\text{V}$	200			

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